

Mahitosh Biswas

List of Publications by Year in descending order

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Version: 2024-02-01

14
papers

76
citations

1684188
5
h-index

1474206
9
g-index

14
all docs

14
docs citations

14
times ranked

100
citing authors

#	ARTICLE	IF	CITATIONS
1	Thermodynamically metastable In_{\pm} , In_{μ} (or In°), and $\text{In}^{\circ 3}$ -Ga ₂ O ₃ : From material growth to device applications. <i>APL Materials</i> , 2022, 10, .	5.1	23
2	Engineering of carrier localization in BGaAs SQW for novel intermediate band solar cells: Thermal annealing effect. <i>Solar Energy</i> , 2020, 199, 183-191.	6.1	12
3	Passivation of Surface States of AlGa _N Nanowires Using H ₃ PO ₄ Treatment To Enhance the Performance of UV-LEDs and Photoanodes. <i>ACS Applied Nano Materials</i> , 2018, 1, 1968-1975.	5.0	9
4	Varying nitrogen background pressure; an efficient approach to improve electrical properties of MBE-grown GaAs _{1-x} N _x thin films with less atomic disorder. <i>Journal of Alloys and Compounds</i> , 2017, 695, 3163-3169.	5.5	7
5	Ultrathin GaAsN matrix-induced reduced full width at half maximum of GaAsN/InAs/GaAsN dot-in-a-well heterostructures with extended emission wavelength. <i>Journal of Luminescence</i> , 2018, 194, 341-345.	3.1	5
6	Defect annihilation-mediated enhanced activation energy of GaAs 0.979 N 0.021 -capped InAs/GaAs quantum dots by H ⁺ ion implantation. <i>Thin Solid Films</i> , 2017, 639, 73-77.	1.8	4
7	Vertical strain-induced dot size uniformity and thermal stability of InAs/GaAsN/GaAs coupled quantum dots. <i>Journal of Alloys and Compounds</i> , 2018, 748, 601-607.	5.5	4
8	Growth of high quality (In,Ga)N films on O-face ZnO substrates by plasma-assisted molecular beam epitaxy. <i>AIP Advances</i> , 2020, 10, .	1.3	4
9	High nitrogen composition-induced low interfacial roughness of GaAs 0.978 N 0.022 /GaAs multiple quantum wells grown through solid-source molecular beam epitaxy. <i>Materials Research Bulletin</i> , 2017, 88, 242-247.	5.2	3
10	Effects of rapid thermal annealing in InGa _N /Ga _N quantum disk-in-GaN nanowire arrays. <i>Journal of Luminescence</i> , 2020, 222, 117123.	3.1	2
11	Annihilation of arsenic-nitrogen bonding defects in annealed InAs _{1-x} N _x quantum dots grown through nitrogen background pressure-controlled SS-MBE. <i>Journal of Alloys and Compounds</i> , 2017, 722, 287-292.	5.5	1
12	A low temperature investigation of the optical properties of coupled InAs quantum dots with GaAsN/GaAs spacers. <i>Proceedings of SPIE</i> , 2017, , .	0.8	1
13	Enhanced optical and structural properties of MBE-grown AlGa _N nanowires on Si substrate by H-ion implantation and UV ozone treatment. , 2019, , .		1
14	CAD Model to Predict the Effect of Radome on the Characteristics of Rectangular Patch Antenna. <i>Microwave and Optical Technology Letters</i> , 2013, 55, 2460-2468.	1.4	0